

*High Voltage Fast-Switching NPN Power Transistor*

### Features

- Very High Switching Speed
- High Voltage Capability
- Wide Reverse Bias SOA



### General Description

This Device is designed for high voltage , High speed switching Characteristics required such as lighting system,switching mode power supply.

### Absolute Maximum Ratings

Symbol	Parameter	Test Conditions	Value	Units
$V_{CES}$	Collector-Emitter Voltage	$V_{BE}=0$	600	V
$V_{CEO}$	Collector-Emitter voltage	$I_B=0$	400	V
$V_{EBO}$	Emitter -Base voltage	$I_C=0$	9.0	V
$I_C$	Collector Current		1.2	A
$I_{CP}$	Collector pulse Current		2.4	A
$I_B$	Base Current		0.75	A
$I_{BM}$	Base Peak Current	$t_P=5ms$	1.5	A
$P_c$	Total Dissipation at $T_c=25^\circ\text{C}$		18	W
$T_J$	Operation Junction Temperature		-40~150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature		-40~150	$^\circ\text{C}$

### Thermal Characteristics

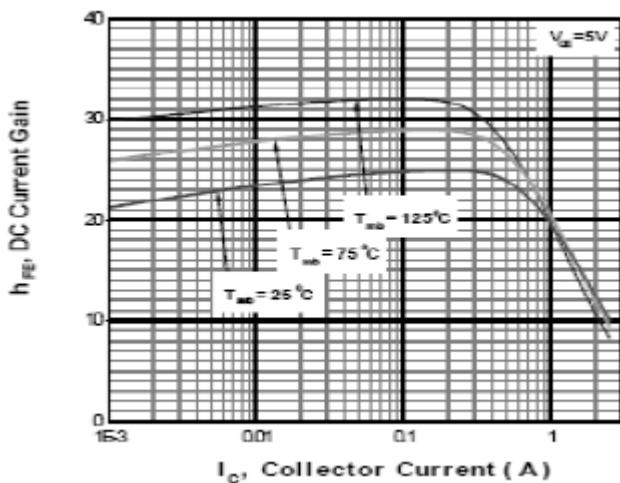
Symbol	Parameter	Value	Units
$R_{QJC}$	Thermal Resistance Junction to Case	6.9	$^\circ\text{C}/\text{W}$
$R_{QJA}$	Thermal Resistance Junction to Ambient	89	

**Electrical Characteristics**( $T_c=25^\circ\text{C}$  unless otherwise noted)

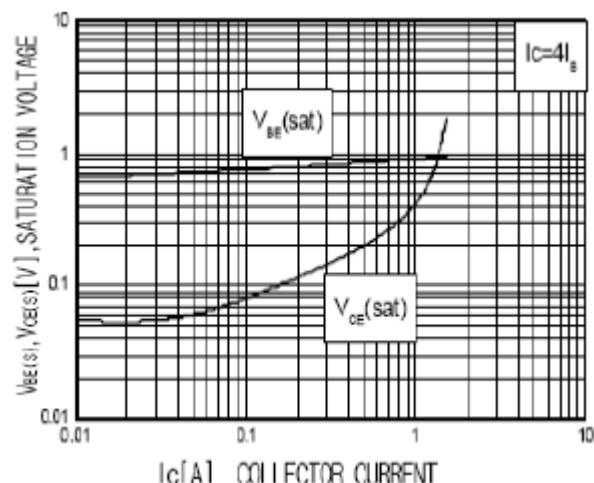
Symbol	Parameter	Test Conditions	Value			Units
			Min	Typ	Max	
$\text{BV}_{\text{CBO}}$	Collector-Base Breakdown Voltage	$I_c=10\text{mA}, I_e=0$	600			V
$\text{BV}_{\text{CEO}}$	Collector-Base Breakdown Voltage	$I_c=10\text{mA}, I_b=0$	400	-	-	V
$V_{\text{CE}(\text{sat})}$	Collector-Emitter Saturation Voltage	$I_c=500\text{mA}, I_b=100\text{mA}$	-	-	0.8	V
$V_{\text{BE}(\text{sat})}$	Base-Emitter Saturation Voltage	$I_c=500\text{mA}, I_b=100\text{mA}$	-	-	1.2	V
$I_{\text{CBO}}$	Collector-Base Cutoff Current	$V_{cb}=600\text{V}, I_e=0\text{mA}$	-	-	5	$\mu\text{A}$
$I_{\text{CEO}}$	Collector-Emitter Cutoff Current	$V_{ce}=400\text{V}, I_b=0\text{mA}$	-	-	10	$\mu\text{A}$
$I_{\text{EBO}}$	Emitter- Base Cutoff Current	$V_{eb}=9\text{V}, I_c=0\text{mA}$	-	-	5	$\mu\text{A}$
$h_{\text{FE}}$	DC Current Gain	$V_{ce}=20\text{V}, I_c=20\text{mA}$	10	-	40	
		$V_{ce}=5\text{V}, I_c=1\text{mA}$	9	-	-	
$t_s$ $t_f$	Storage Time Fall Time	$V_{cc}=24\text{V}$ $I_c=5I_B$ $I_{B1}=-I_{B2}=0.05\text{A}$	-	-	4	$\mu\text{s}$
			-	-	0.7	
$f_T$	Characteristic frequency	$V_{ce}=10\text{V}, I_c=0.1\text{A}$	4	-	-	MHz

Note:

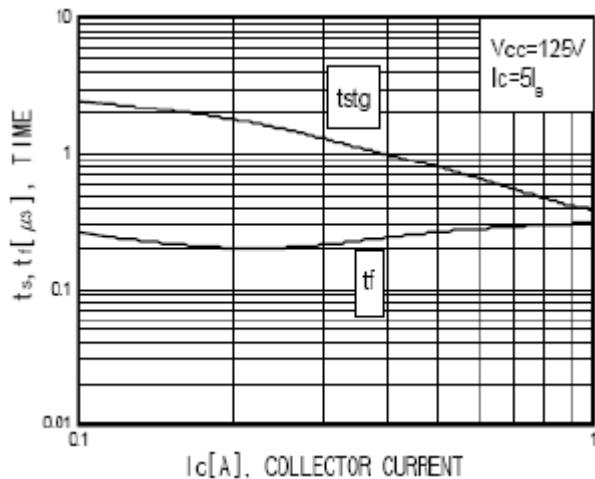
Pulse Test : Pulse width 300,Duty cycle 2%



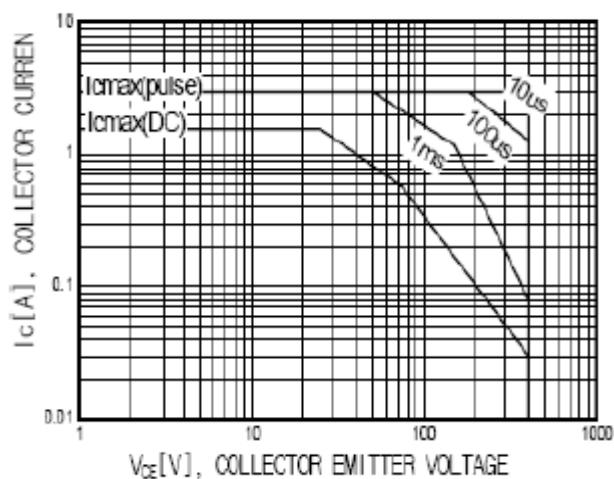
**Fig.1 DC Current Gain**



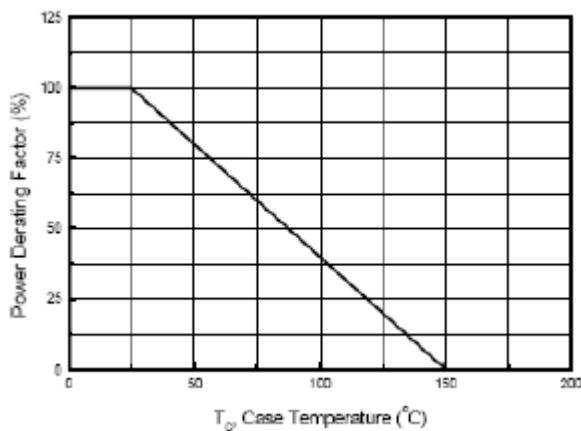
**Fig.2 Saturation Voltage**



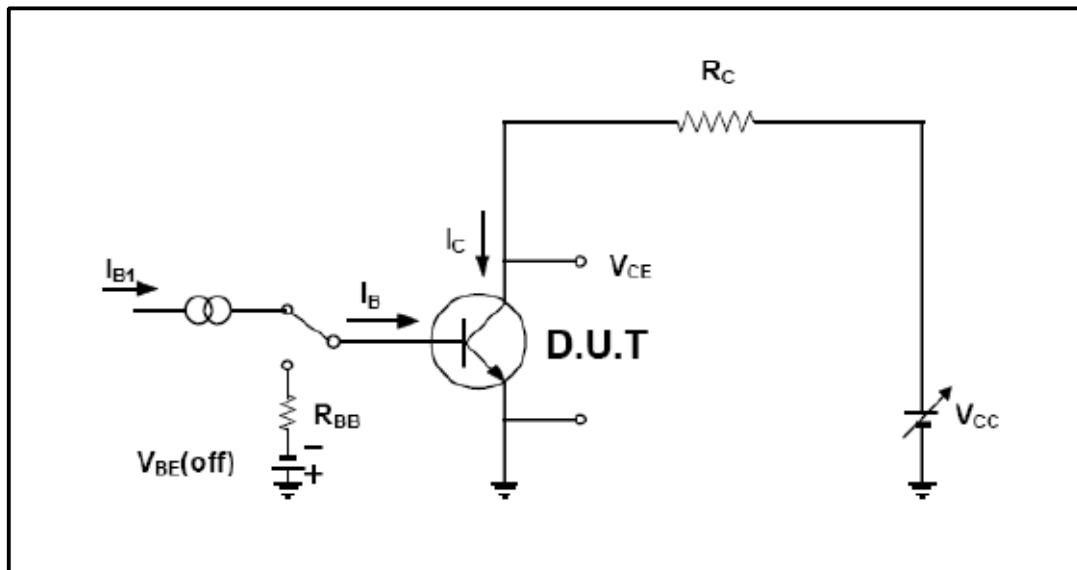
**Fig.3 Switching time**



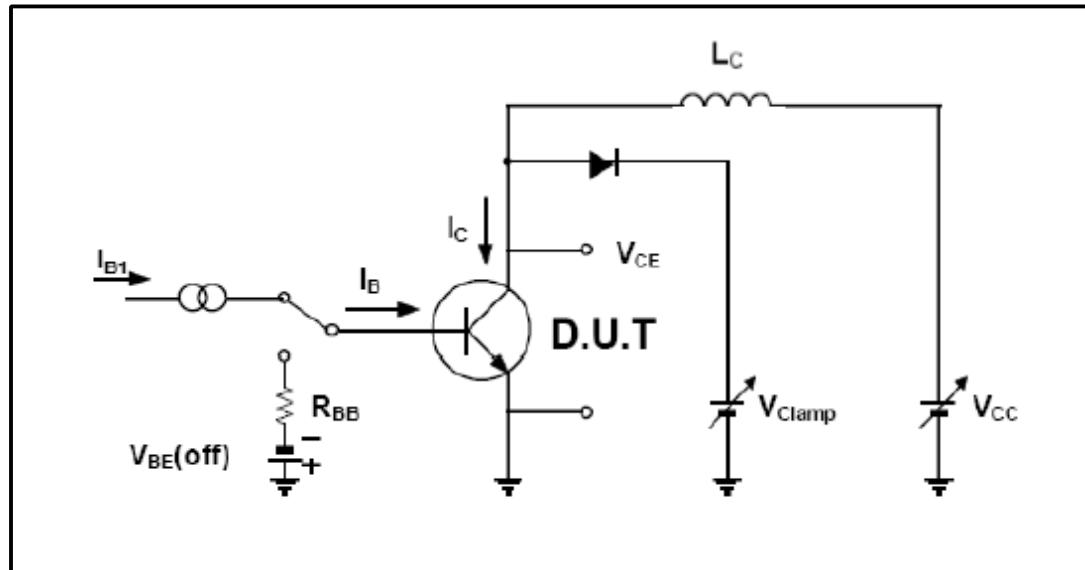
**Fig.4 Safe Operation Area**



**Fig.6 Power Derating**



**Resistive Load Switching Test Circuit**



**Inductive Load Switching & RBSOA Test Circuit**

**To-92 Package Dimension**

